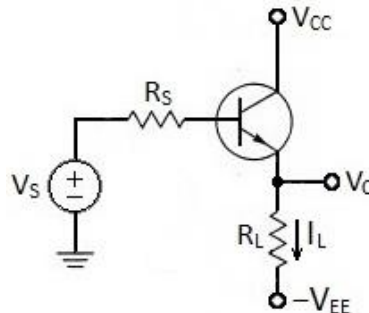


## TUTORIAL-VIII

### SEM-III, B.Tech(Computer Engineering), SVNIT, Surat

#### Topic: BJT and its characteristics

- 1) Derive the expression of transistor currents, take PNP transistor biased in active region.
- 2) The given relation between  $\alpha$  and  $\beta$ ,  $\alpha = \frac{\beta}{1+\beta}$  then  
 $\beta = \underline{\hspace{2cm}}$ ,  $1+\beta = \underline{\hspace{2cm}}$ ,  $(1-\alpha) = \underline{\hspace{2cm}}$ .
- 3) Draw output characteristics of NPN silicon transistor in CE configuration. Indicate cut off, saturation and active regions.
- 4) Draw input characteristics of PNP silicon transistor in CE configuration.
- 5) Draw output characteristics of PNP silicon transistor in CB configuration. Indicate cut off, saturation and active regions.
- 6) Draw input characteristics of NPN silicon transistor in CB configuration.
- 7) A silicon transistor is operating in active region with  $\alpha = 0.975$ . If emitter current is 2 mA and reverse saturation current is 0.1  $\mu$ A at a temperature of 25° C, determine the leakage current and the remaining currents of transistor at a temperature of 65° C.
- 8) Calculate the  $I_B$  and  $I_C$  for transistor if  $I_E = 5 \text{ mA}$ ,  $I_{CEO} = 0.15 \text{ mA}$  and  $\beta = 100$ .
- 9) For the given BJT circuit, calculate the current  $I_L$ , if  $V_S = 5 \text{ V}$ ,  $R_S = 430 \text{ K}\Omega$ ,  $R_L = 2.2 \text{ K}\Omega$ ,  $\beta = 100$ ,  $V_{CC} = 5 \text{ V}$  and  $-V_{EE} = -5 \text{ V}$ . Neglect leakage current.



- 10) Repeat the Q-9 by considering  $R_C = 2.2 \text{ K}\Omega$ .